

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device includes a substrate which is made of, e.g., silicon and which has in its principal surface first and second recessed portions formed at a distance from each other. Disposed in the first recessed portion is a first semiconductor
5 laser chip in the form of a function block, which emits an infrared laser beam. Disposed in the second recessed portion is a second semiconductor laser chip in the form of a function block, which emits a red laser beam.